

Amendments to the Specification:

Please replace the paragraph beginning at page 10, line 3 with the following amended paragraph:

[0035] Wafer stage 355 moves wafer 350 while reflected light is detected in detector 370. An output of detector ~~270~~ 370 may be provided to a data processor such as a computer 380 (or the data processor may be integrated with the detector). The output may be related to a characteristic of the reflected light incident on detector 370, such as an intensity or an interference pattern.

Please replace the paragraph beginning at page 12, line 11 with the following amended paragraph:

[0043] Prior to aligning the reticle and wafer according to a method such as that illustrated in FIG. 4, the alignment pattern (or patterns) are fabricated on the wafer. For example, the alignment patterns may be fabricated at the same time trenches for shallow trench isolation (STI) structures are formed. FIG. 5 shows a cross section of a region 500 of a wafer with an alignment pattern including alignment features 510A and 520A. Features 510A and ~~520A~~ 510B are formed by etching a trench in a silicon substrate 520, growing a thick SiO<sub>2</sub> layer, and polishing the SiO<sub>2</sub> layer back to the surface of substrate 520.